

Title (en)

EPITAXIAL METHODS AND STRUCTURES FOR FORMING SEMICONDUCTOR MATERIALS

Title (de)

EPITAXIALVERFAHREN UND STRUKTUREN ZUR BILDUNG VON HALBLEITERMATERIALIEN

Title (fr)

PROCÉDÉS D'ÉPITAXIE ET STRUCTURES ÉPITAXIALES POUR FORMER DES MATÉRIAUX SEMI-CONDUCTEURS

Publication

EP 2412006 A1 20120201 (EN)

Application

EP 09785805 A 20090105

Priority

IB 2009000228 W 20090205

Abstract (en)

[origin: WO2010089623A1] Methods and structures for producing semiconductor materials, substrates and devices with improved characteristics are disclosed. Structures and methods for forming reduced strain structures include forming a plurality of substantially strain relaxed island structures and utilizing such island structures for subsequent further growth of strain relaxed substantial continuous layers of semiconductor material.

IPC 8 full level

H01L 21/205 (2006.01)

CPC (source: EP KR)

C30B 25/18 (2013.01 - EP); **C30B 29/403** (2013.01 - EP); **C30B 29/406** (2013.01 - EP); **H01L 21/0242** (2013.01 - EP); **H01L 21/02458** (2013.01 - EP); **H01L 21/02502** (2013.01 - EP); **H01L 21/0254** (2013.01 - EP); **H01L 21/02639** (2013.01 - EP); **H01L 21/02647** (2013.01 - EP); **H01L 21/0265** (2013.01 - EP); **H01L 21/20** (2013.01 - KR)

Citation (search report)

See references of WO 2010089623A1

Citation (examination)

WO 2009015350 A1 20090129 - SOITEC SILICON ON INSULATOR [FR], et al

Cited by

EP2837763A1; DE102013108848A1

Designated contracting state (EPC)

AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO SE SI SK TR

DOCDB simple family (publication)

WO 2010089623 A1 20100812; CN 102308369 A 20120104; EP 2412006 A1 20120201; JP 2012517114 A 20120726; KR 20110102501 A 20110916; SG 173524 A1 20110929

DOCDB simple family (application)

IB 2009000228 W 20090205; CN 200980156217 A 20090205; EP 09785805 A 20090105; JP 2011548791 A 20090205; KR 20117018170 A 20090205; SG 2011055969 A 20090205